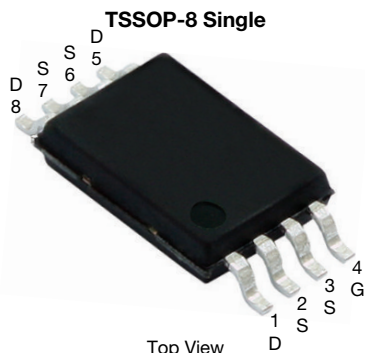


## P-Channel 20 V (D-S) MOSFET



Top View

### FEATURES

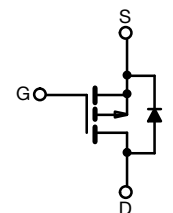
- TrenchFET® power MOSFET
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Load switch
- Battery switch
- Power management



P-Channel MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	-20
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5$ V	0.0098
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -2.5$ V	0.0130
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -1.8$ V	0.0227
$Q_g$ typ. (nC)	63
$I_D$ (A) <sup>d</sup>	-12.5
Configuration	Single

### ORDERING INFORMATION

Package	TSSOP-8
Lead (Pb)-free and halogen-free	Si6423ADQ-T1-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	-20	V
Gate-source voltage	$V_{GS}$	$\pm 8$	V
Continuous drain current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_C = 25$ °C	-12.5
		$T_C = 70$ °C	-10
		$T_A = 25$ °C	-10.3 <sup>a, b</sup>
		$T_A = 70$ °C	-8.2 <sup>a, b</sup>
Pulsed drain current ( $t = 300$ $\mu$ s)	$I_{DM}$	-70	A
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C	-1.9
		$T_A = 25$ °C	-1.3
Avalanche current	$I_{AS}$	-20	A
Single pulse avalanche energy	$E_{AS}$	20	mJ
Maximum power dissipation	$P_D$	$T_C = 25$ °C	2.2
		$T_C = 70$ °C	1.4
		$T_A = 25$ °C	1.5 <sup>a, b</sup>
		$T_A = 70$ °C	1.0 <sup>a, b</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a, c</sup>	$R_{thJA}$	65	83	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	46	56	°C/W

#### Notes

- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- Maximum under steady state conditions is 120 °C/W
- $T_C = 25$  °C



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = -250 μA	-	-11	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	2.9	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.4	-	-1	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	-	-	-1	μA
		V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	-10	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -10 V	-10	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -10 A	-	0.0082	0.0098	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -8 A	-	0.0108	0.0130	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -5 A	-	0.0175	0.0227	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -10 A	-	70	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	5875	-	pF
Output capacitance	C <sub>oss</sub>		-	540	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	555	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -8 V, I <sub>D</sub> = -16.7 A	-	112	168	nC
			-	63	95	
Gate-source charge	Q <sub>gs</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -16.7 A	-	8.7	-	
Gate-drain charge	Q <sub>gd</sub>		-	25.3	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.8	3.6	7.2	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -10 V, R <sub>L</sub> = 1 Ω, I <sub>D</sub> ≡ -10 A, V <sub>GEN</sub> = -8 V, R <sub>g</sub> = 1 Ω	-	12	24	ns
Rise time	t <sub>r</sub>		-	4	8	
Turn-off delay time	t <sub>d(off)</sub>		-	120	180	
Fall time	t <sub>f</sub>		-	36	54	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	-18	A
Pulse diode forward current <sup>a</sup>	I <sub>SM</sub>		-	-	-70	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = -10 A	-	-0.75	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = -10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	45	68	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	38	57	nC
Reverse recovery fall time	t <sub>a</sub>		-	18	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	27	-	

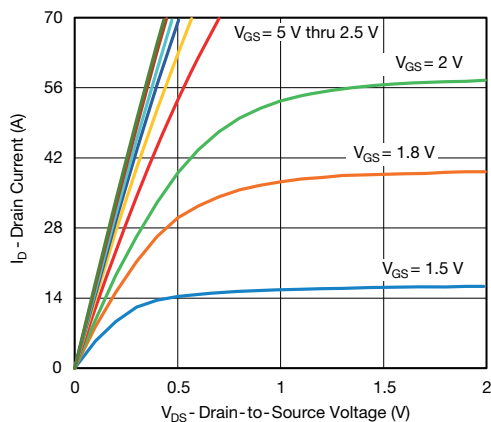
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

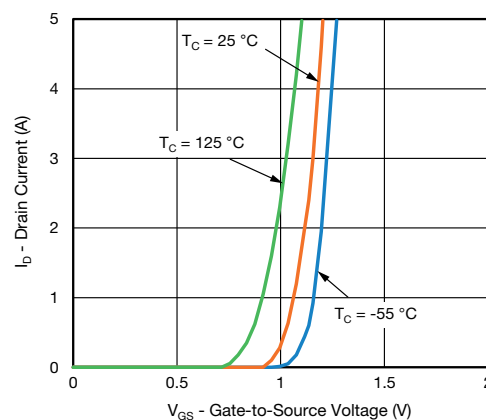
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



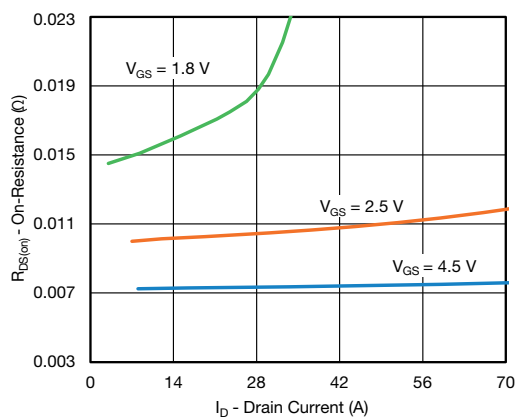
**TYPICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)



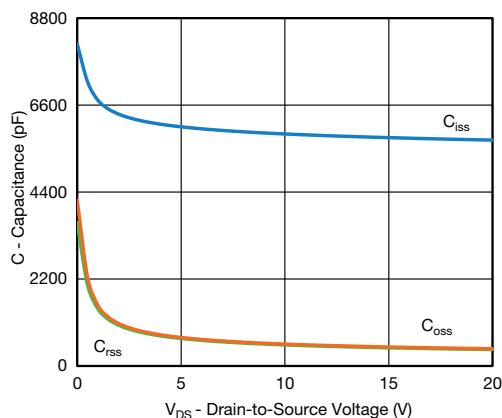
**Output Characteristics**



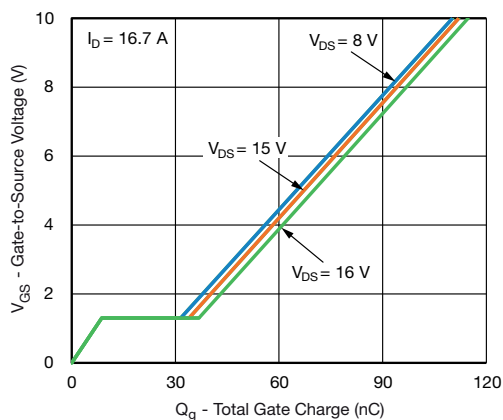
**Transfer Characteristics**



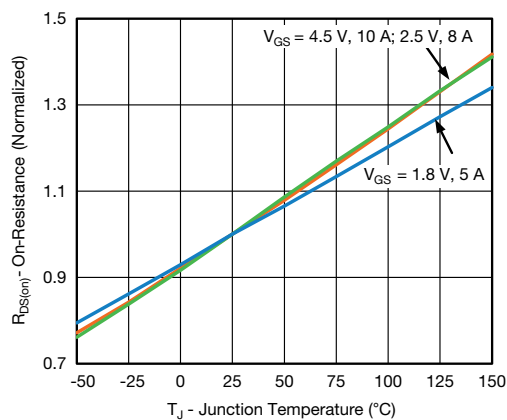
**On-Resistance vs. Drain Current**



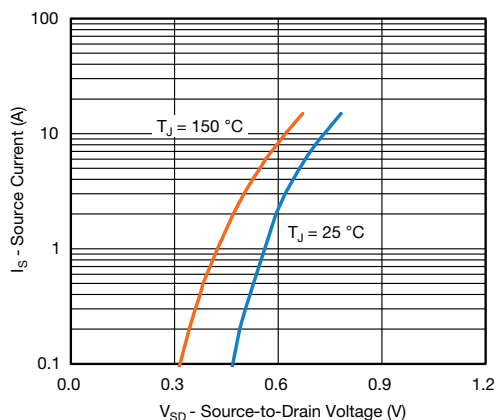
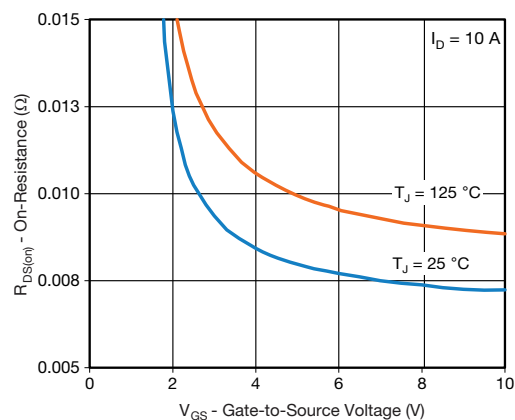
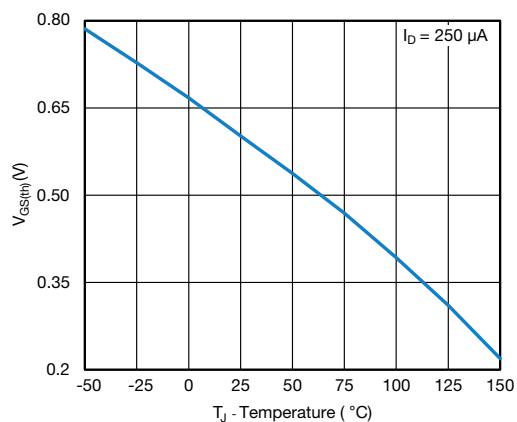
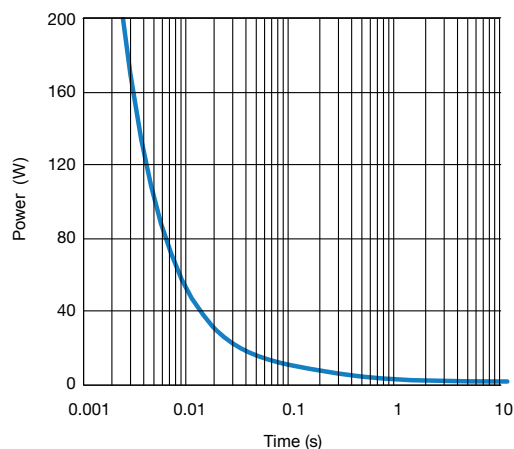
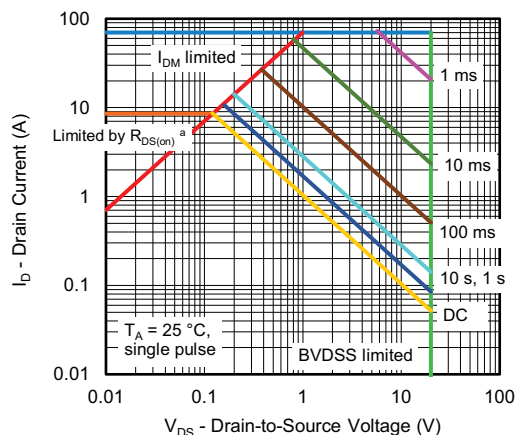
**Capacitance**



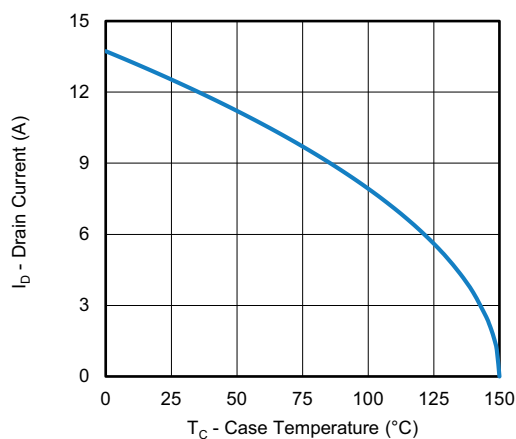
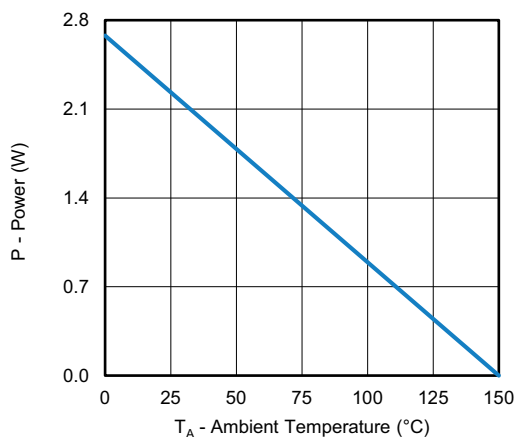
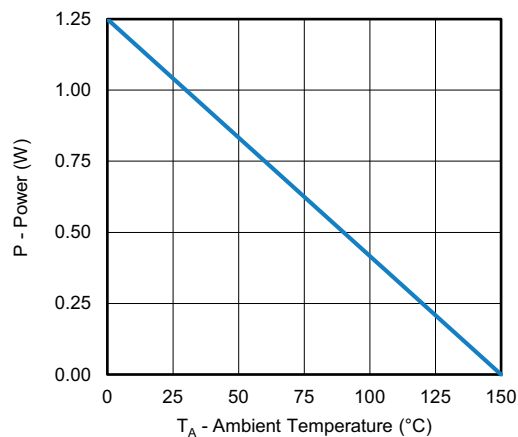
**Gate Charge**



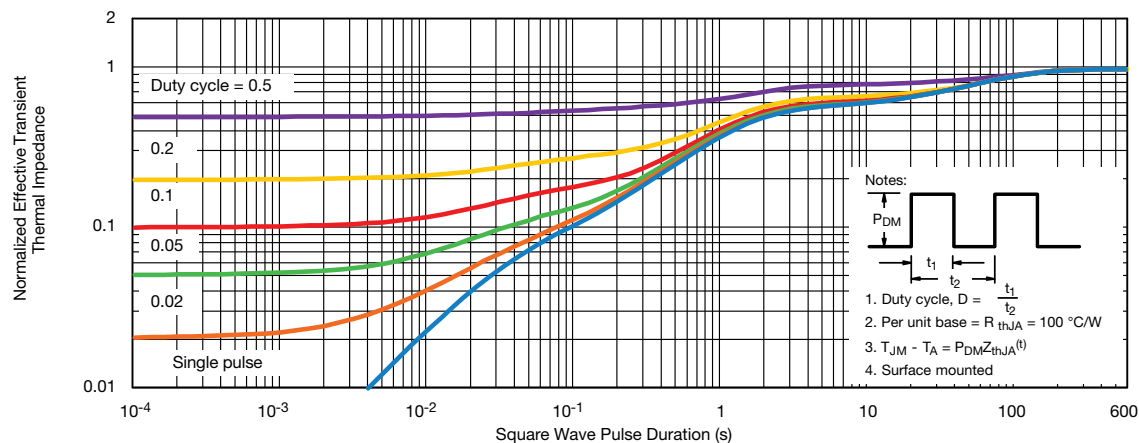
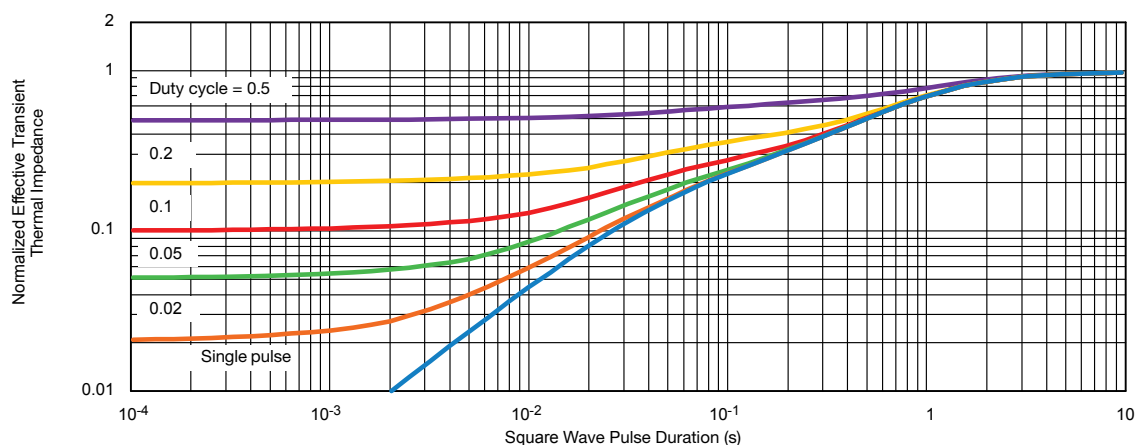
**Normalized On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Source-Drain Diode Forward Voltage**

**On-Resistance vs. Gate-to-Source Voltage**

**Threshold Voltage**

**Single Pulse Power, Junction-to-Ambient**

**Safe Operating Area, Junction-to-Ambient**
**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**TYPICAL CHARACTERISTICS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Current Derating <sup>a</sup>**

**Power, Junction-to-Case**

**Power, Junction-to-Ambient**
**Note**

- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

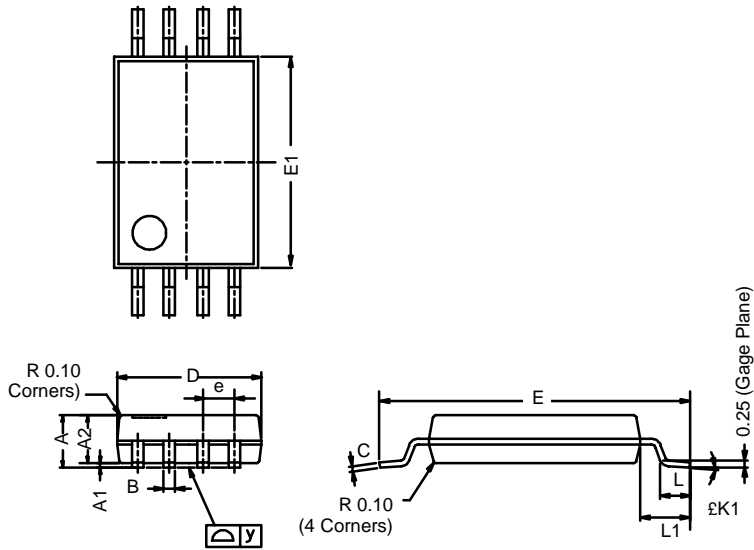
**TYPICAL CHARACTERISTICS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**Normalized Thermal Transient Impedance, Junction-to-Case**

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### TSSOP: 8-LEAD

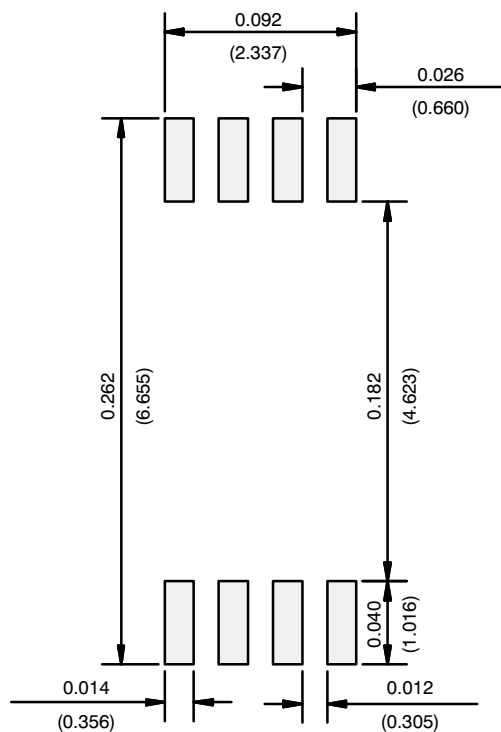
JEDEC Part Number: MO-153



Dim	MILLIMETERS		
	Min	Nom	Max
A	—	—	1.20
A <sub>1</sub>	0.05	0.10	0.15
A <sub>2</sub>	0.80	1.00	1.05
B	0.19	0.28	0.30
C	—	0.127	—
D	2.90	3.00	3.10
E	6.20	6.40	6.60
E <sub>1</sub>	4.30	4.40	4.50
e	—	0.65	—
L	0.45	0.60	0.75
L <sub>1</sub>	0.90	1.00	1.10
Y	—	—	0.10
$\epsilon K1$	0°	3°	6°

ECN: S-03946—Rev. G, 09-Jul-01  
DWG: 5844

## RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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